

FETs, IPD, IGBTs, GaAs MMICs

■ Power Transistor Arrays (F-MOS FETs)

Application	Part No.	Absolute Maximum Ratings ($T_C = 25^\circ\text{C}$)				Electrical Characteristics ($T_a = 25^\circ\text{C}$)				Package	No.
		V_{DSS} (V)	V_{GSS} (V)	I_D (A)	P_D (W)	$R_{DS(on)}$ max. (mΩ)	$ Y_{fs} $ typ. (S)	t_{on} typ.* (ns)	t_f typ. (ns)		
Non-contact solenoid drive. Motor drive. Control equipment switching equipment.	PUB4753 (PU7457)	100 ± 5	± 20	± 3	15	450/600♦	4	0.2	0.3	1.5	SIP10-A1
	PUB4701	150^*	$\pm 20^*$	$\pm 6^*$	15*	0.6*/0.7*♦	5.3*	10*	8.5*	290*	
	PUB4702	$35 \pm 10^*$	$\pm 15^*$	$\pm 1^*$		380/680*♦	1*	120*	390*	800*	

*: $T_a=25^\circ\text{C}$ ♦: Rating of low voltage drive ($V_{GS} = 4\text{ V}$)

■ Silicon Junction FETs

Application	Package (Package No.)								Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)		Electrical Characteristics ($T_a = 25^\circ\text{C}$)	
	ML3-N2 (D1)	SSSMini3-F1 (D5)	SSSMini3-F2 (D9)	SMini3-G1 (D17)	MiniT3-F1 (D27)	Mini3-G1 (D26)	NS-A1/ NS-B1 (D61/D62)	TO-92-A1 (D56)	V_{DSO} * V_{GDS} (V)	I_D (mA)	$NV \times NF$ max. *typ. (mV)	I_{DSS} max. (mA)
General-use low-frequency amplifier	—	—	—	2SJ0364 (2SJ364)		2SK1103 2SJ0163 (2SJ163)	2SK1104 2SJ0164 (2SJ164)	—	*-65	20	—	6
General-use	—	—	2SK2593	2SK0662 (2SK662) 2SK0663 (2SK663)		2SK0198 (2SK198)	—	$V_{GDO} -30$	20	*60	12	
Capacitor microphone	2SK3578	2SK3372 2SK3585 2SK3426	—	—	2SK1860 2SK3584 2SK3427	2SK0123 (2SK123) 2SK3583	—	$V_{GDO} -55$	30	*2.5 dB	20	
Infrared sensor		△ 2SK3396	2SK2380	—		2SK1842 2SK2751	—	2SK0301 (2SK301)	30	*0.5 dB	20	
								20	2	0.004	0.4	
								20	0.1	0.004	0.47	
								20	2	0.01	0.4	
								-12	2	0.004	0.8	
								$V_{GDO} -40$	1	$C_{iss} * 1\text{ pF}$	0.2	
								*-40	10	—	4.7	

Δ: Tentative 1) S-A1 (D61)

Note) In the tables, part numbers show the Matsushita unified part numbers. And the part numbers in parentheses show the conventional ones.